

SILICON EPITAXIAL PLANAR DIODE

Band Switching Diode

Features

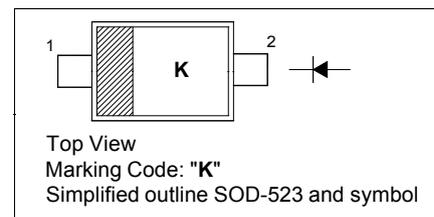
- Extremely small surface mounting type
- High reliability

Applications

- High frequency switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	35	V
Forward Current	I_F	100	mA
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	1	V
Reverse Current at $V_R = 25\text{ V}$	I_R	10	nA
Capacitance Between Terminals at $V_R = 6\text{ V}$, $f = 1\text{ MHz}$	C_T	1.2	pF
Forward Operating Resistance at $I_F = 2\text{ mA}$, $f = 100\text{ MHz}$	R_F	0.7	Ω

1SS270

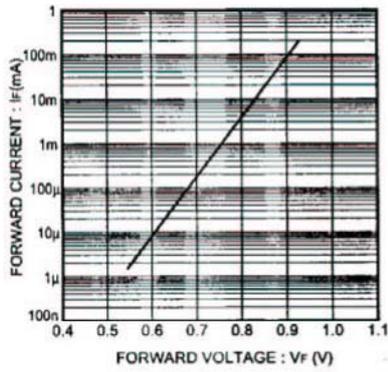


Fig. 1 Forward characteristics

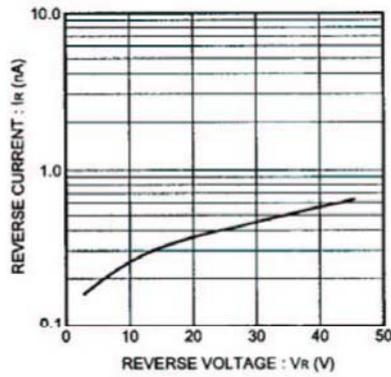


Fig. 2 Reverse characteristics

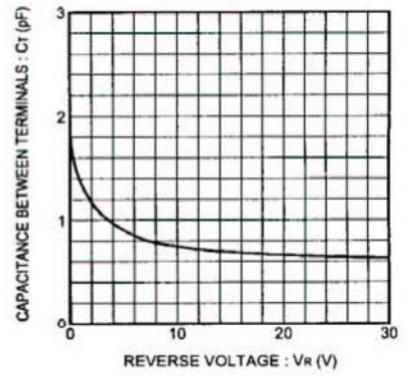


Fig. 3 Capacitance between terminals characteristics

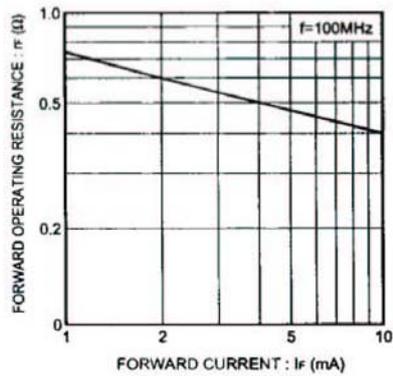


Fig. 4 Forward operating resistance characteristics